

Tandem 600V HYPERFAST BOOST DIODE

MAJOR PRODUCTS CHARACTERISTICS

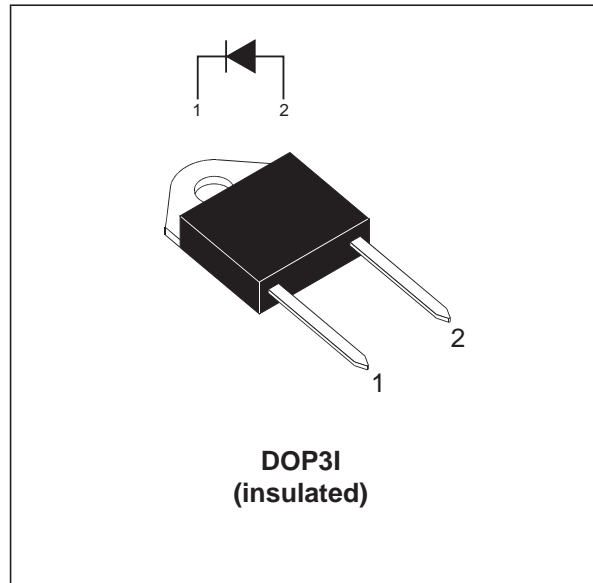
$I_{F(AV)}$	15 A
V_{RRM}	600 V
$T_j(max)$	150 °C
$V_F(max)$	2.4 V
$I_{RM}(typ.)$	4.8 A
$t_{rr}(typ.)$	16 ns

FEATURES AND BENEFITS

- ESPECIALLY SUITED AS BOOST DIODE IN CONTINUOUS MODE POWER FACTOR CORRECTORS AND HARD SWITCHING CONDITIONS
- DESIGNED FOR HIGH DI/DT OPERATION. HYPERFAST RECOVERY CURRENT TO COMPETE WITH SIC DEVICES. ALLOWS DOWNSIZING OF MOSFET AND HEATSINKS
- INTERNAL CERAMIC INSULATED DEVICES WITH EQUAL THERMAL CONDITIONS FOR BOTH 300V DIODES
- INSULATION (2500V_{RMS}) ALLOWS PLACEMENT ON SAME HEATSINK AS MOSFET AND FLEXIBLE HEATSINKING ON COMMON OR SEPARATE HEATSINK
- STATIC AND DYNAMIC EQUILIBRIUM OF INTERNAL DIODES ARE WARRANTED BY DESIGN
- PACKAGE CAPACITANCE: C=16pF

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		600	V
$I_{F(RMS)}$	RMS forward current		26	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10\text{ ms}$ sinusoidal	130	A
I_{peak}	Peak current waveform	$\delta = 0.15$ $T_c = 120^\circ\text{C}$	35	A
T_{stg}	Storage temperature range		-65 +150	°C
T_j	Maximum operating junction temperature		+ 150	°C



DESCRIPTION

The TURBOSWITCH "H" is an ultra high performance diode composed of two 300V dice in series. TURBOSWITCH "H" family drastically cuts losses in the associated MOSFET when run at high di_F/dt .

STTH1506DPI

THERMAL AND POWER DATA

Symbol	Parameter	Test conditions	Value	Unit
$R_{th(j-c)}$	Junction to case		1.6	°C/W

STATIC ELECTRICAL CHARACTERISTICS (for both diodes)

Symbol	Parameter	Tests Conditions	Min.	Typ.	Max.	Unit
I_R^*	Reverse leakage current	$V_R = V_{RRM}$	$T_j = 25^\circ\text{C}$		20	μA
			$T_j = 125^\circ\text{C}$		30	
V_F^{**}	Forward voltage drop	$I_F = 15\text{ A}$	$T_j = 25^\circ\text{C}$		3.6	V
			$T_j = 150^\circ\text{C}$		1.95	

Pulse test: * $t_p = 100\text{ms}$, $\delta < 2\%$

** $t_p = 380\mu\text{s}$, $\delta < 2\%$

To evaluate the maximum conduction losses use the following equation:

$$P = 1.7 \times I_{F(AV)} + 0.047 \times I_{F(RMS)}^2$$

RECOVERY CHARACTERISTICS

Symbol	Parameter	Tests Conditions	Min.	Typ.	Max.	Unit	
t_{rr}	Reverse recovery time	$I_F = 0.5\text{ A}$ $I_{rr} = 0.25\text{ A}$ $I_R = 1\text{ A}$	$T_j = 25^\circ\text{C}$		16	ns	
		$I_F = 1\text{ A}$ $dI_F/dt = -50\text{ A}/\mu\text{s}$ $V_R = 30\text{ V}$					35
I_{RM}	Reverse recovery current	$V_R = 400\text{ V}$ $I_F = 15\text{ A}$ $dI_F/dt = -200\text{ A}/\mu\text{s}$	$T_j = 125^\circ\text{C}$		4.8	6.0	A
S	Reverse recovery softness factor				0.4		-
Q_{rr}	Reverse recovery charges				80		nC

TURN-ON SWITCHING CHARACTERISTICS

Symbol	Parameter	Tests Conditions	Min.	Typ.	Max.	Unit
t_{fr}	Forward recovery time	$I_F = 15\text{ A}$ $dI_F/dt = 100\text{ A}/\mu\text{s}$, $V_{FR} = 1.1 \times V_{Fmax}$	$T_j = 25^\circ\text{C}$		200	ns
V_{FP}	Forward recovery voltage	$I_F = 15\text{ A}$ $dI_F/dt = 100\text{ A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		6	V

Fig. 1: Conduction losses versus average current.

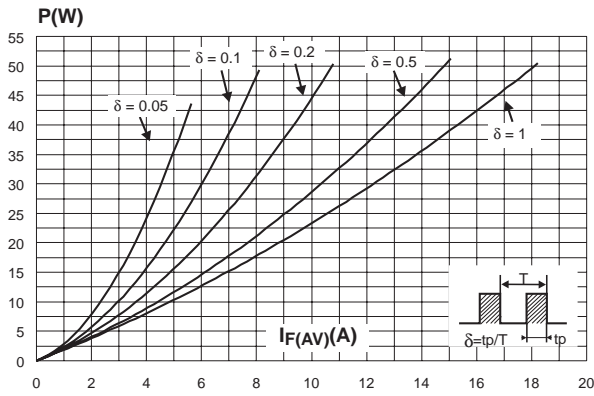


Fig. 2: Forward voltage drop versus forward current.

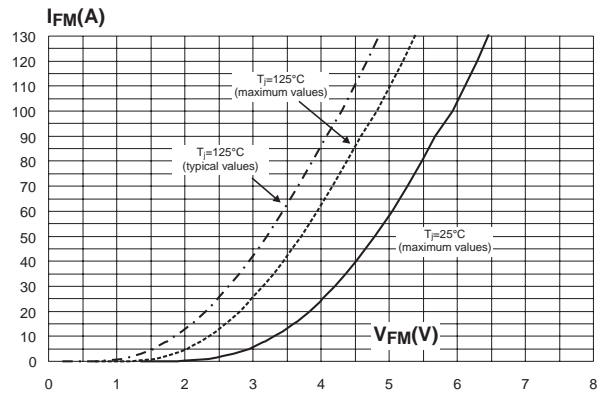


Fig. 3: Relative variation of thermal impedance junction to case versus pulse duration.

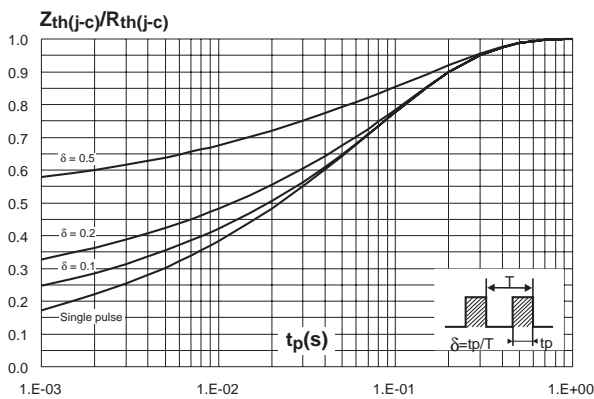


Fig. 4: Peak reverse recovery current versus di_F/dt (typical values).

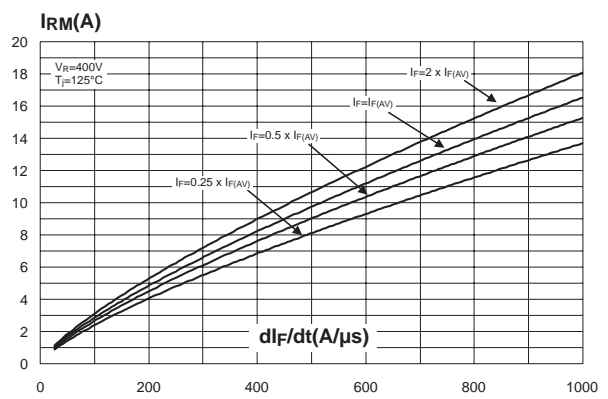


Fig. 5: Reverse recovery time versus di_F/dt (typical values).

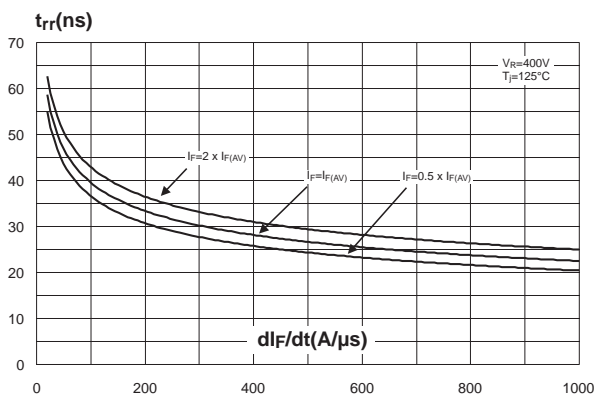


Fig. 6: Reverse recovery charges versus di_F/dt (typical values).

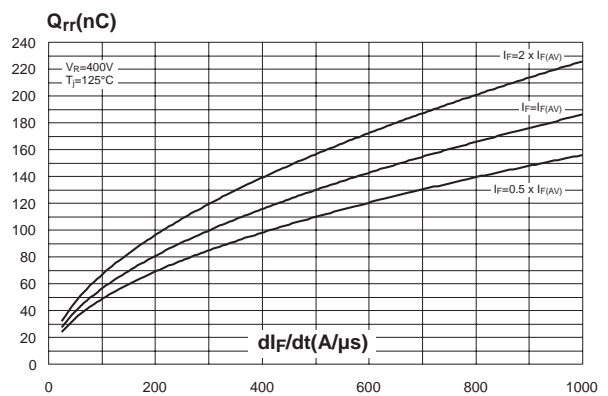


Fig. 7: Softness factor versus di_F/dt (typical values).

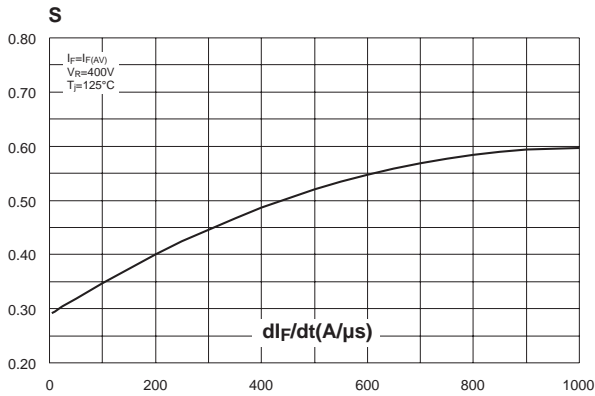


Fig. 8: Relative variations of dynamic parameters versus junction temperature.

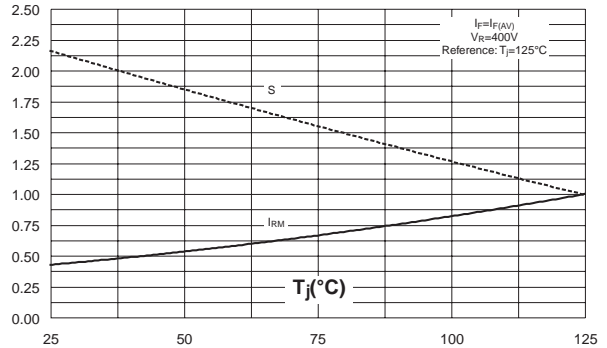


Fig. 9: Transient peak forward voltage versus di_F/dt (typical values).

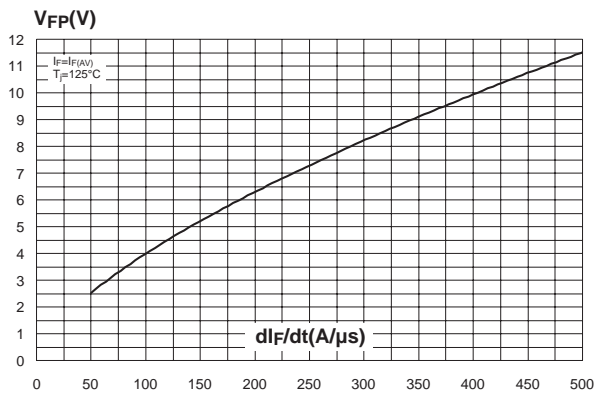


Fig. 10: Forward recovery time versus di_F/dt (typical values).

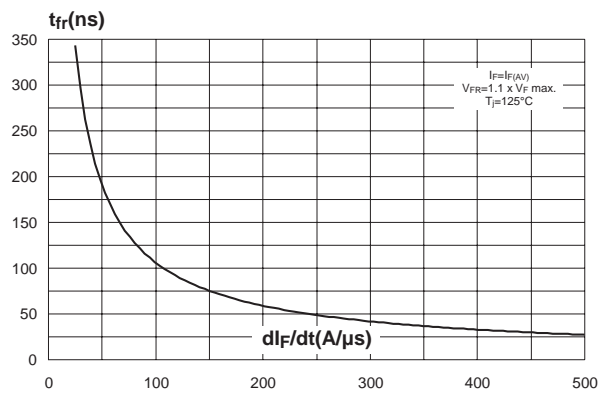
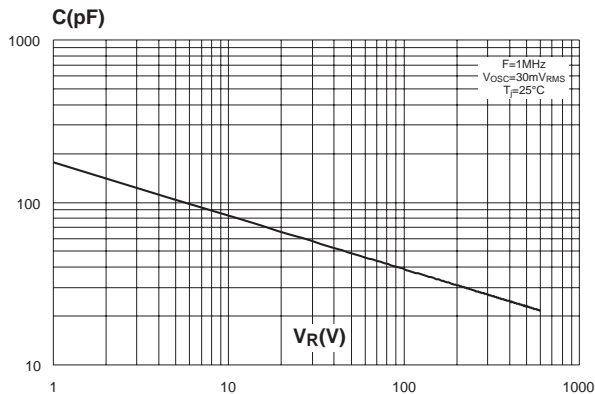


Fig. 11: Junction capacitance versus reverse voltage applied (typical values).



PACKAGE MECHANICAL DATA
 DOP3I

REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.4	4.6	0.173	0.181
B	1.45	1.55	0.057	0.061
C	14.35	15.60	0.565	0.614
D	0.5	0.7	0.020	0.028
E	2.7	2.9	0.106	0.114
F	15.8	16.5	0.622	0.650
G	20.4	21.1	0.815	0.831
H	15.1	15.5	0.594	0.610
K	3.4	3.65	0.134	0.144
L	4.08	4.17	0.161	0.164
N	10.8	11.3	0.425	0.444
P	1.20	1.40	0.047	0.055
R	4.60 typ.		0.181 typ.	

Ordering code	Marking	Package	Weight	Base qty	Delivery mode
STTH1506DPI	STTH1506DPI	DOP3I	4.46 g.	30	Tube

- Epoxy meets UL94,V0

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